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Publications

Parts of this work have already been published:
Journal Publications

- I. Hengel, A. Neisser, R. Klenk, M. Ch. Lux-Steiner.
  Current transport in $CuInS_2$:Ga/CdS/ZnO-solar cells.
  Thin Solid Films. 361–362:458–462, 2000
- A. Neisser, I. Hengel, R. Klenk, Th.W. Matthes, J. Alvarez-García and A. Perez-Rodríguez, A. Romano-Rodríguez, M.-Ch. Lux-Steiner.
  Effect of Ga incorporation in sequentially prepared $CuInS_2$ thin film absorbers.
  Solar Energy Materials and Solar Cells. 67:97–104, 2001.
- J. Alvarez-García, J.R. Morante, A. Perez-Rodríguez, A. Romano-Rodríguez, L. Calvo-Barrio, R.Scheer, R. Klenk, A. Neisser.
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Conference Proceedings

- A. Neisser, J. Alvarez-García, L. Calvo-Barrio, R. Klenk, Th.W. Matthes, I. Luck, M.Ch. Lux-Steiner, A. Pérez-Rodríguez, J.R. Morante.
  $Cu(In,Ga)S_2$ Phase Formation from Metallic Cu-In-Ga Precursor Stacks in Rapid Thermal Processes.
  Mat. Res. Soc. Symp. Proc. 668:H.1.3.1, 2001.
- Th. Riedle, Th.W. Matthes, A. Neisser, R. Klenk, C. Hinrichs, N. Esser, W. Richter, M. Ch. Lux-Steiner.
  Preparation of $CuInS_2$ absorber layers by rapid thermal sulfurization using H_2S and DTBS.
  Proceedings of 16th EPVSEC, Glasgow.:713–716, 2000.

Poster Presentations

- Th. Riedle, A. Neisser, K. Otte, R. Klenk, N. Esser, W. Richter, M. Ch. Lux-Steiner.
  Ramanspektroskopie an dünnen $Cu(In,Ga)S_2$ - Absorberschichten für Solarzellen.
  presented at DPG Frühjahrstagung, Hamburg, 2001.